

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

# TLP504A, TLP504A-2

PROGRAMMABLE CONTROLLERS

AC/DC-INPUT MODULE

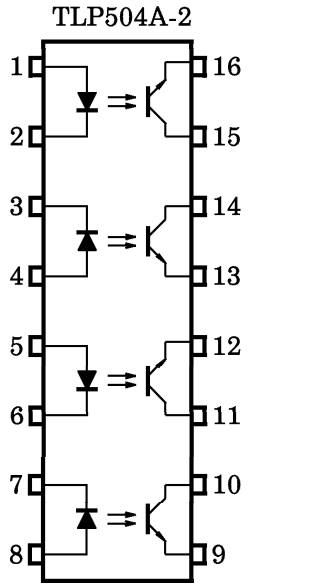
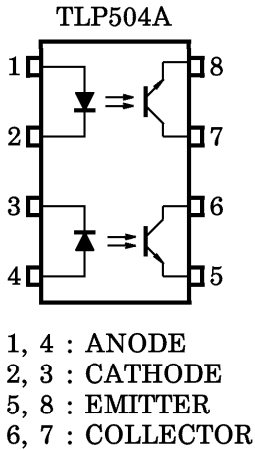
SOLID STATE RELAY

The TOSHIBA TLP504A and TLP504A-2 consists of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode.

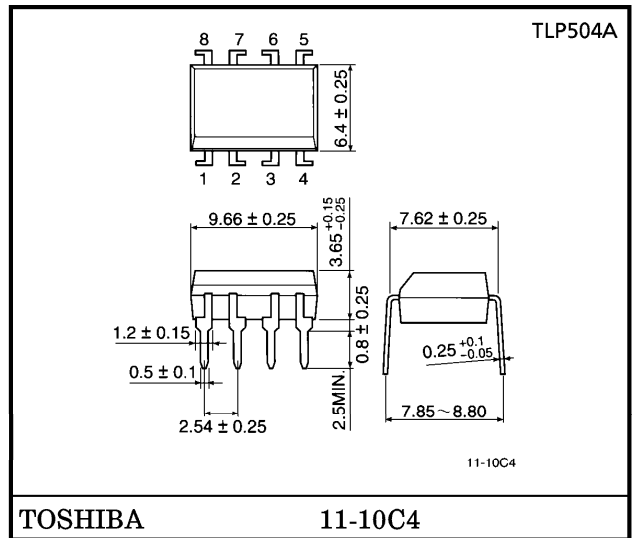
The TLP504A offers two isolated channels in a eight lead plastic DIP package, while the TLP504A-2 provides four isolated channels in a sixteen plastic DIP package.

- Collector-Emitter Voltage : 55V (Min.)
- Current Transfer Ratio : 50% (Min.)  
Rank GB : 100% (Min.)
- Isolation Voltage : 2500Vrms (Min.)
- UL Recognized : UL1577,  
File No. E67349

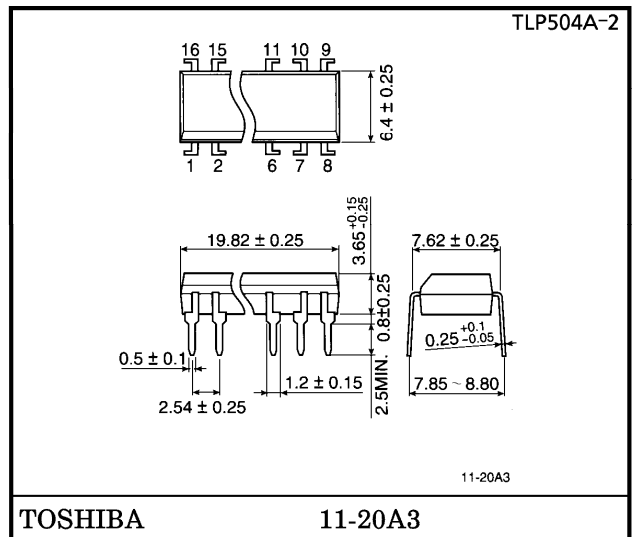
**PIN CONFIGURATIONS (TOP VIEW)**



Unit in mm



Weight : 0.54g



Weight : 1.1g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING		UNIT
			TLP504A	TLP504A-2	
LED	Forward Current	$I_F$	60	50	mA
	Forward Current Derating	$\Delta I_F / ^\circ\text{C}$	-0.7 (Ta $\geq$ 39°C)	-0.5 (Ta $\geq$ 25°C)	mA / °C
	Pulse Forward Current	$I_{FP}$	1 (100 $\mu$ s pulse, 100pps)		A
	Reverse Voltage	$V_R$	5		V
	Junction Temperature	$T_j$	125		°C
DETECTOR	Collector-Emitter Voltage	$V_{CEO}$	55		V
	Emitter-Collector Voltage	$V_{ECO}$	7		V
	Collector Current	$I_C$	50		mA
	Collector Power Dissipation (1 Circuit)	$P_C$	150	100	mW
	Collector Power Dissipation Derating (1 Circuit Ta $\geq$ 25°C)	$\Delta P_C / ^\circ\text{C}$	-1.5	-1.0	mW / °C
	Junction Temperature	$T_j$	125		°C
Storage Temperature Range		$T_{stg}$	-55~150		°C
Operating Temperature Range		$T_{opr}$	-55~100		°C
Lead Soldering Temperature		$T_{sol}$	260 (10s)		°C
Total Package Power Dissipation		$R_T$	250	150	mW
Total Package Power Dissipation Derating (Ta $\geq$ 25°C)		$\Delta P_T / ^\circ\text{C}$	-2.5	-1.5	mW / °C
Isolation Voltage		$BV_S$	2500 (AC, 1min., R.H. $\leq$ 60%) (Note 1)		Vrms

(Note 1) Device considered a two terminal device : LED side pins shorted together and DETECTOR side pins shorted together.

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	$V_{CC}$	—	5	24	V
Forward Current	$I_F$	—	16	20	mA
Collector Current	$I_C$	—	1	10	mA
Operating Temperature	$T_{opr}$	-25	—	85	°C

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	$V_F$	$I_F = 10\text{mA}$	1.0	1.15	1.3	V
	Reverse Current	$I_R$	$V_R = 5\text{V}$	—	—	10	$\mu\text{A}$
	Capacitance	$C_T$	$V = 0, f = 1\text{MHz}$	—	30	—	pF
DETECTOR	Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 0.5\text{mA}$	55	—	—	V
	Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	$I_E = 0.1\text{mA}$	7	—	—	V
	Collector Dark Current	$I_{CEO}$	$V_{CE} = 24\text{V}$	—	10	100	nA
			$V_{CE} = 24\text{V}, T_a = 85^\circ\text{C}$	—	2	50	$\mu\text{A}$
Capacitance Collector to Emitter	$C_{CE}$	$V = 0, f = 1\text{MHz}$	—	10	—	pF	

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	$I_C / I_F$	$I_F = 5\text{mA}, V_{CE} = 5\text{V}$ Rank GB	50	—	600	%
			100	—	600	
Saturated CTR	$I_C / I_F (\text{sat})$	$I_F = 1\text{mA}, V_{CE} = 0.4\text{V}$ Rank GB	—	60	—	%
			30	—	—	
Collector-Emitter Saturation Voltage	$V_{CE} (\text{sat})$	$I_C = 2.4\text{mA}, I_F = 8\text{mA}$ $I_C = 0.2\text{mA}, I_F = 1\text{mA}$ Rank GB	—	—	0.4	V
			—	0.2	—	
			—	—	0.4	

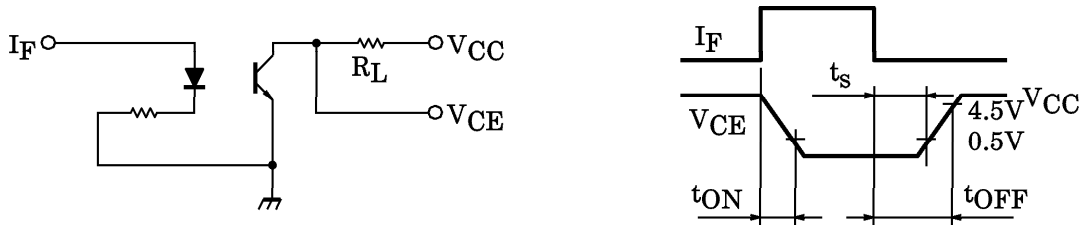
ISOLATION CHARACTERISTICS (Ta = 25°C)

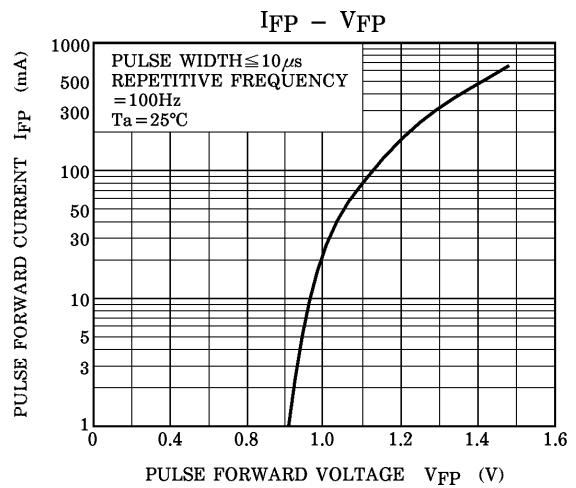
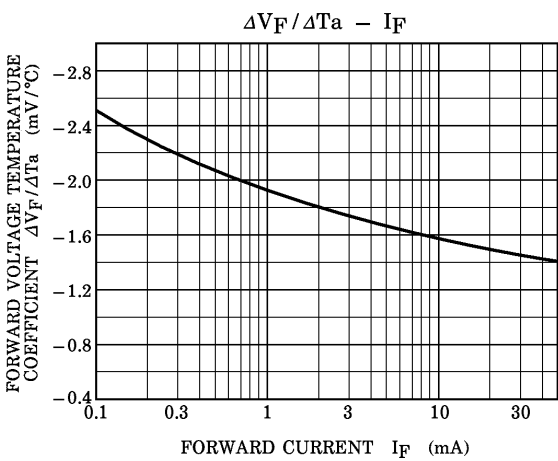
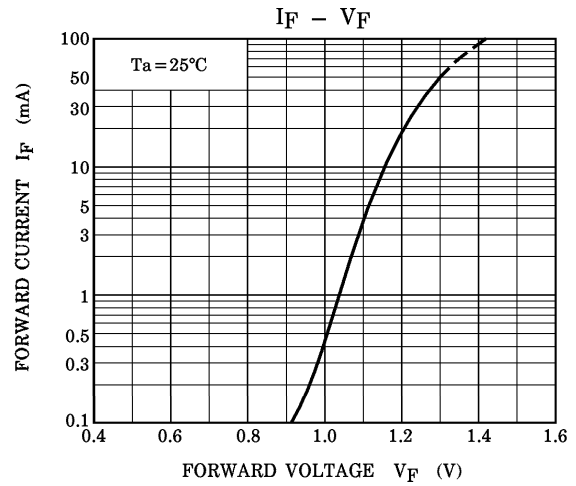
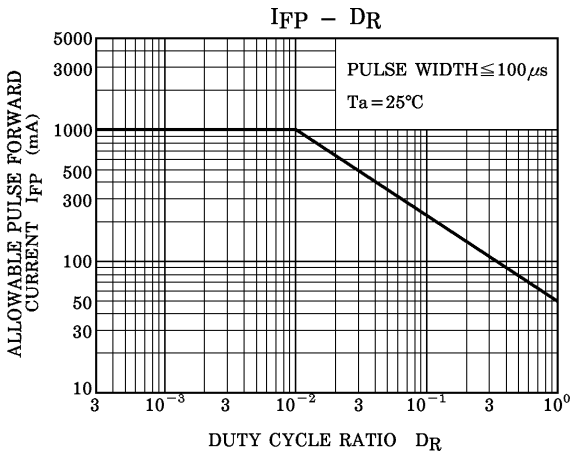
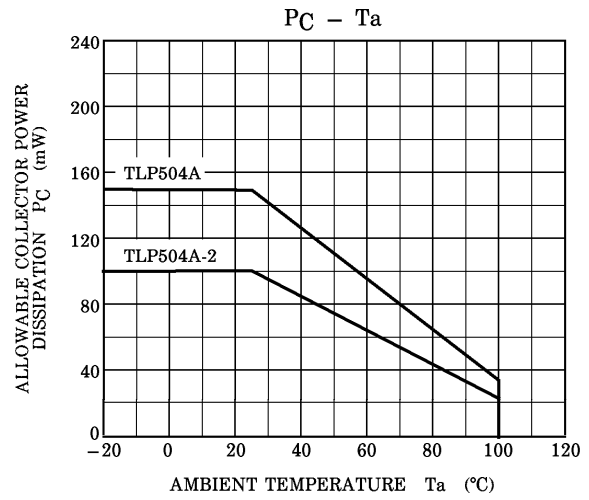
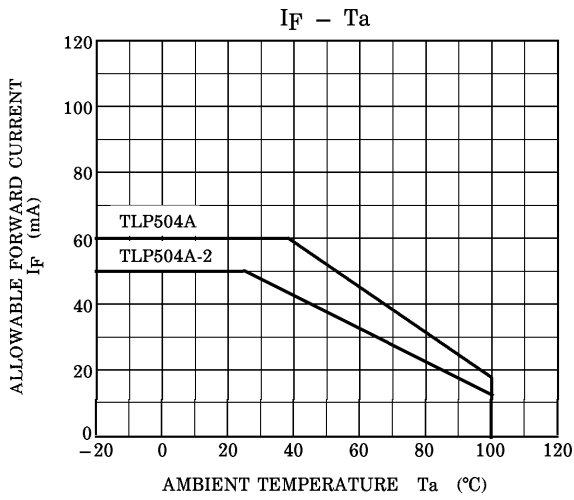
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance Input to Output	$C_S$	$V_S = 0, f = 1\text{MHz}$	—	0.8	—	pF
Isolation Resistance	$R_S$	$V_S = 500\text{V}$	$5 \times 10^{10}$	$10^{14}$	—	$\Omega$
Isolation Voltage	$BV_S$	AC, 1 minute	2500	—	—	$V_{\text{rms}}$
		AC, 1 second, in oil	—	5000	—	
		DC, 1 minute, in oil	—	5000	—	Vdc

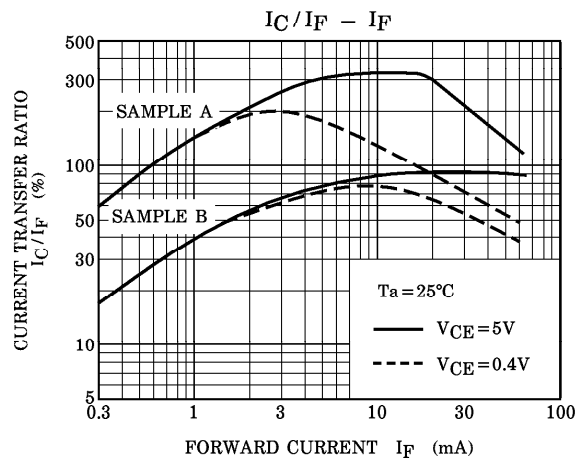
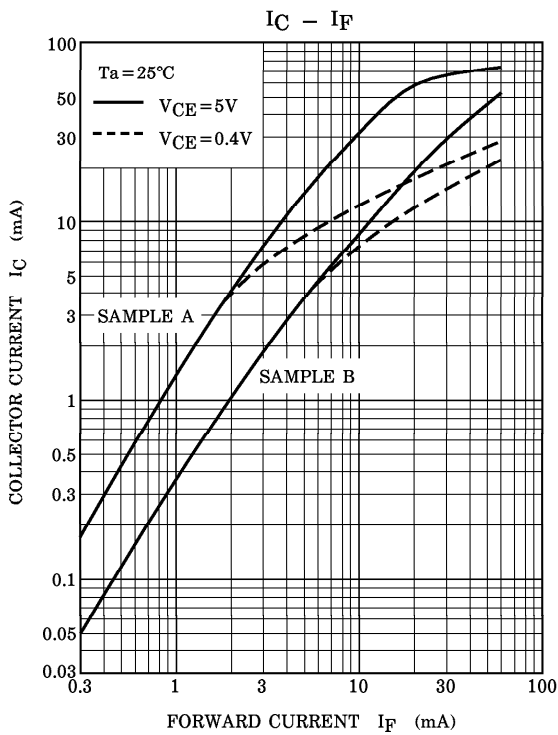
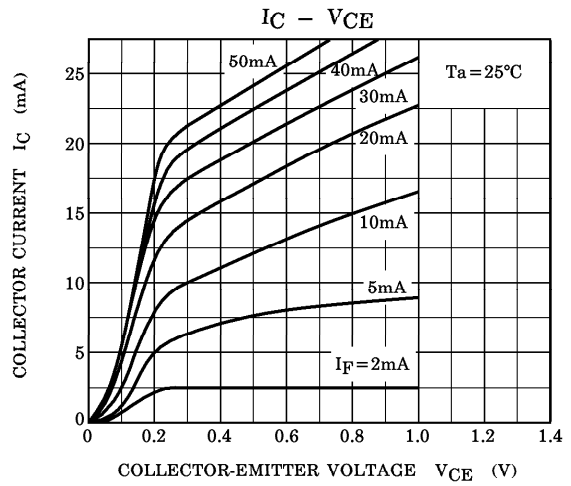
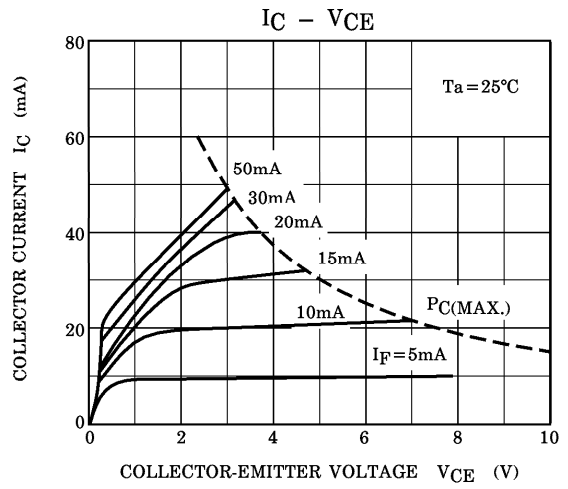
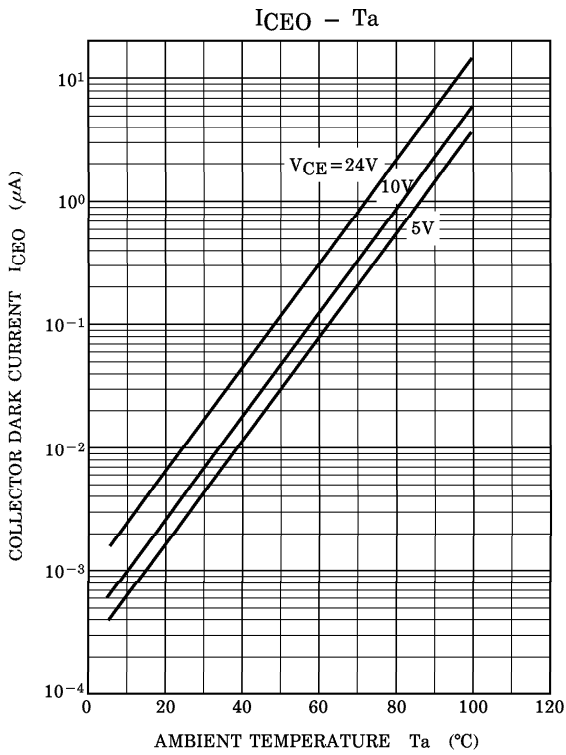
SWITCHING CHARACTERISTICS (Ta = 25°C)

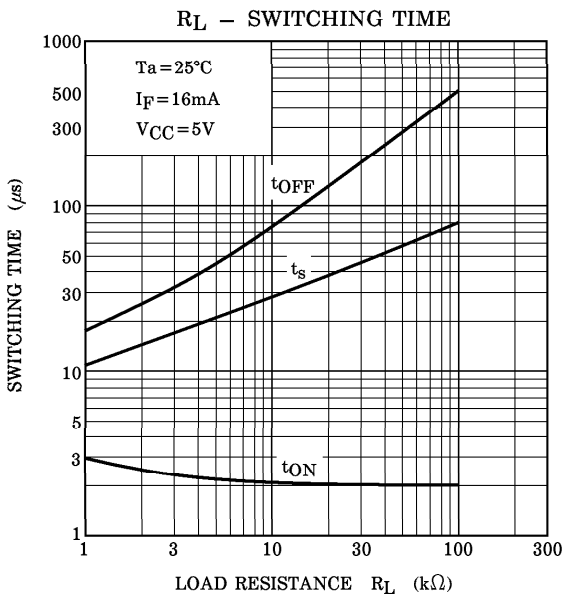
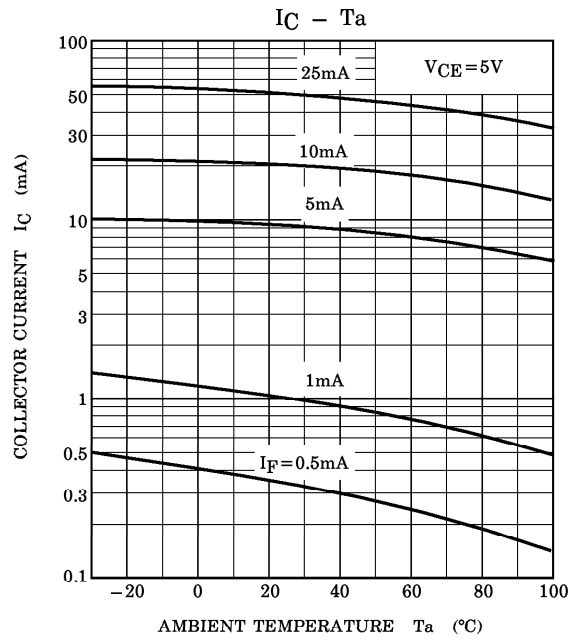
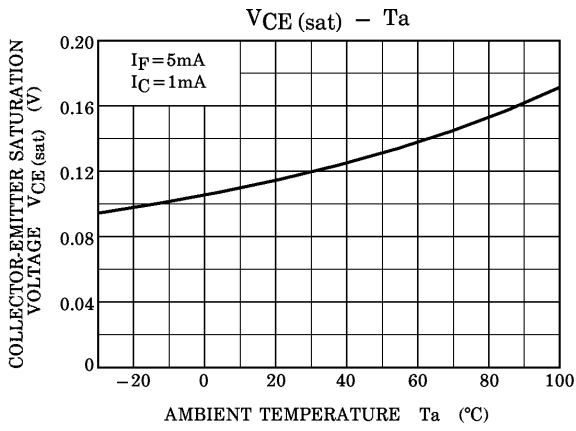
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	$t_r$	$V_{CC} = 10V, I_C = 2mA$ $R_L = 100\Omega$	—	2	—	$\mu S$
Fall Time	$t_f$		—	3	—	
Turn-on Time	$t_{on}$		—	3	—	
Turn-off Time	$t_{off}$		—	3	—	
Turn-on Time	$t_{ON}$	$R_L = 1.9k\Omega$ (Fig.1) $V_{CC} = 5V, I_F = 16mA$	—	2	—	$\mu S$
Storage Time	$t_s$		—	15	—	
Turn-off Time	$t_{OFF}$		—	25	—	

Fig.1 Switching Time Test Circuit









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